NEW PRODUCT

DMN30H4D0LFDE

N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

$V_{(BR)DSS}$	$R_{DS(ON)}$	I_D T_A = +25°C
300V	4Ω @ V_{GS} = 10V	0.55A
	4Ω @ V_{GS} = 4.5V	0.55A
	6Ω @ V_{GS} = 2.7V	0.44A

Description

This new generation MOSFET has been designed to minimize the on-state resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- Power management functions
- Battery Operated Systems and Solid-State Relays
- Drivers: Relays, Solenoids, Lamps, Hammers, Displays, Memories, Transistors, etc

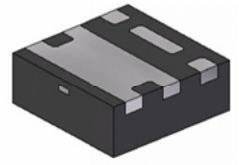
Features

- 0.6mm profile – ideal for low profile applications
- PCB footprint of 4mm^2
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

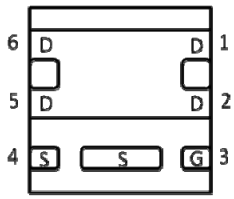
Mechanical Data

- Case: U-DFN2020-6
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – NiPdAu over Copper leadframe. Solderable per MIL-STD-202, Method 208 e4
- Weight: 0.0065 grams (approximate)

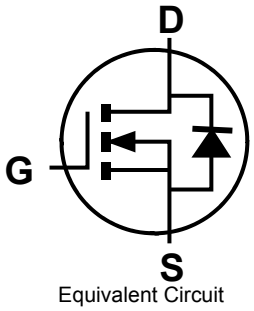
U-DFN2020-6



Bottom View



Pin Out
Bottom View



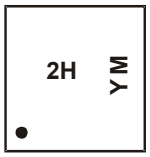
Equivalent Circuit

Ordering Information (Note 4)

Part Number	Compliance	Case	Quantity per reel
DMN30H4D0LFDE-7	Standard	U-DFN2020-6	3,000
DMN30H4D0LFDE-13	Standard	U-DFN2020-6	10,000

Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



2H = Product Type Marking Code
YM = Date Code Marking
Y = Year (ex: A = 2013)
M = Month (ex: 9 = September)

Date Code Key

Year	2013	2014	2015	2016	2017	2018	2019
Code	A	B	C	D	E	F	G

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

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Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V_{DSS}	300	V
Gate-Source Voltage			V_{GSS}	±20	V
Continuous Drain Current (Note 6) V_{GS} = 10V	Steady State	T_A = +25°C T_A = +70°C	I_D	0.55 0.43	A
Pulsed Drain Current (10µs pulse, duty cycle ≦1%)			I_{DM}	2	A
Maximum Body Diode Continuous Current (Note 6)			I_S	2	A

Thermal Characteristics

Characteristic		Symbol	Value	Units
Total Power Dissipation	(Note 5)	P_D	0.63	W
	(Note 6)		1.98	
Thermal Resistance, Junction to Ambient	(Note 5)	$R_{\theta JA}$	189	°C/W
	(Note 6)		61	
Thermal Resistance, Junction to Case	(Note 6)	$R_{\theta JC}$	9.3	
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	300	—	—	V	V_{GS} = 0V, I_D = 250µA
Zero Gate Voltage Drain Current	I_{DSS}	—	—	1	µA	V_{DS} = 240V, V_{GS} = 0V
Gate-Body Leakage	I_{GSS}	—	—	±100	nA	V_{GS} = ±20V, V_{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(th)}$	1	1.7	2.8	V	V_{DS} = V_{GS}, I_D = 250µA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	2.3	4	Ω	V_{GS} = 10V, I_D = 0.3A
		—	2.3	4		V_{GS} = 4.5V, I_D = 0.2A
		—	2.4	6		V_{GS} = 2.7V, I_D = 0.1A
Diode Forward Voltage	V_{SD}	—	0.7	1.2	V	V_{GS} = 0V, I_S = 0.3A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C_{iss}	—	187.3	—	pF	V_{DS} = 25V, V_{GS} = 0V, f = 1MHz
Output Capacitance	C_{oss}	—	11.7	—		
Reverse Transfer Capacitance	C_{rss}	—	8.7	—		
Total Gate Charge	Q_g	—	7.6	—	nC	V_{DS} = 192V, V_{GS} = 10V, I_D = 0.5A
Gate-Source Charge	Q_{gs}	—	0.5	—		
Gate-Drain Charge	Q_{gd}	—	3.3	—		
Turn-On Delay Time	$t_{D(on)}$	—	4.9	—	nS	V_{DS} = 60V, R_L =200Ω V_{GS} = 10V, R_G = 25Ω
Turn-On Rise Time	t_r	—	4.7	—		
Turn-Off Delay Time	$t_{D(off)}$	—	25.8	—		
Turn-Off Fall Time	t_f	—	17.5	—		

Notes: 5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
7. Short duration pulse test used to minimize self-heating effect
8. Guaranteed by design. Not subject to production testing

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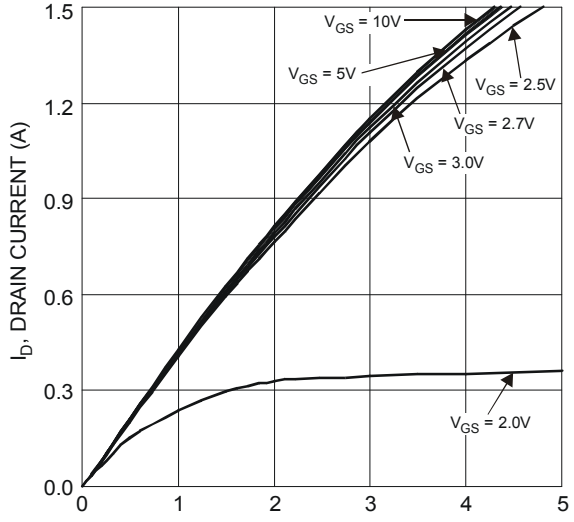

Figure 1 Typical Output Characteristics

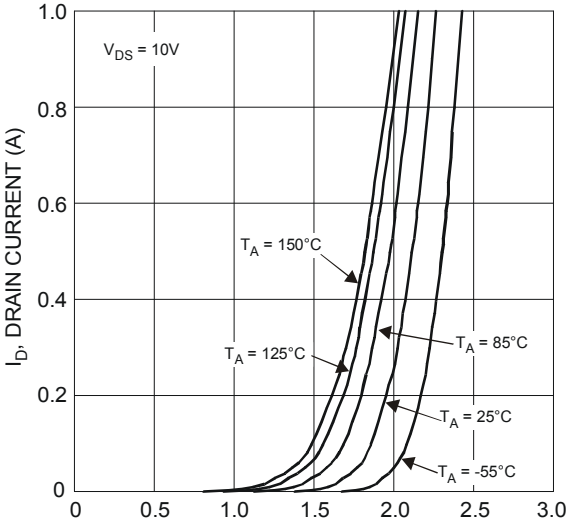

Figure 2 Typical Transfer Characteristics

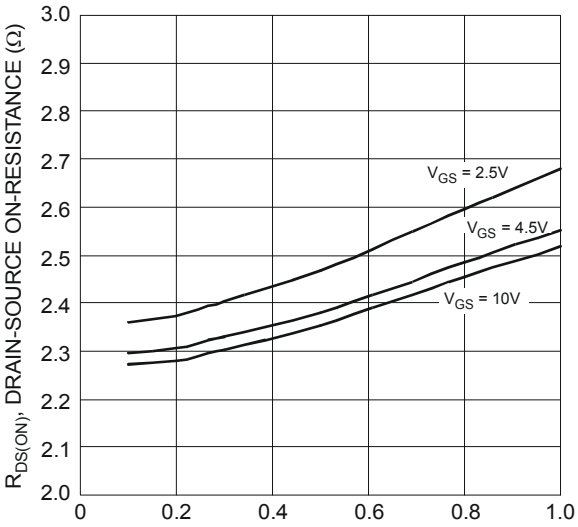

Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

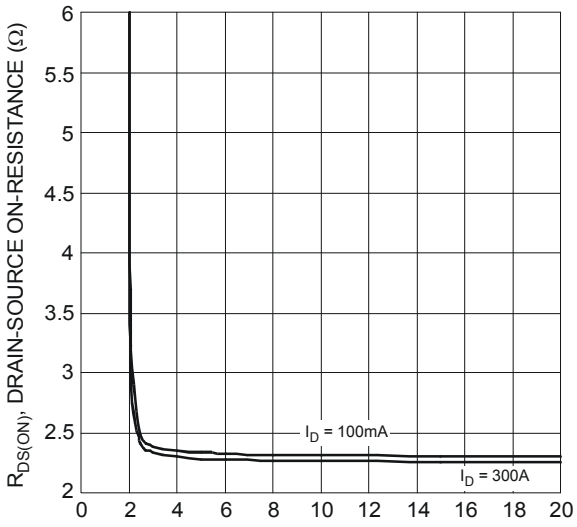

Figure 4 Typical Transfer Characteristics

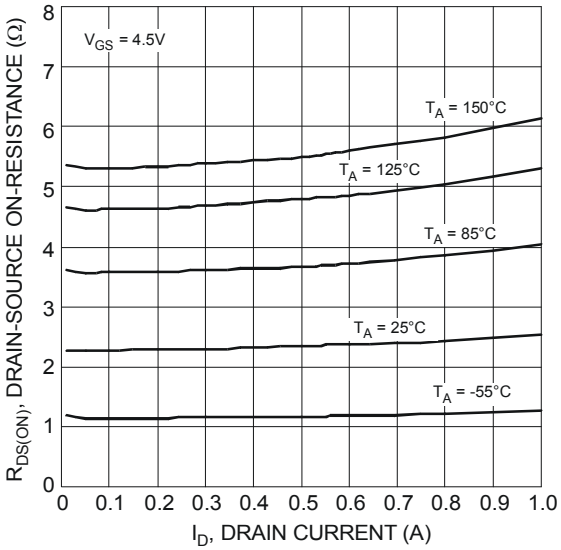

Figure 5 Typical On-Resistance vs. Drain Current and Temperature

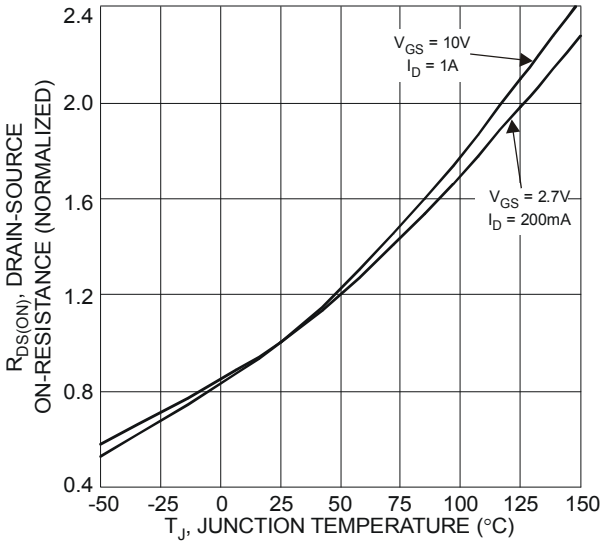

Figure 6 On-Resistance Variation with Temperature

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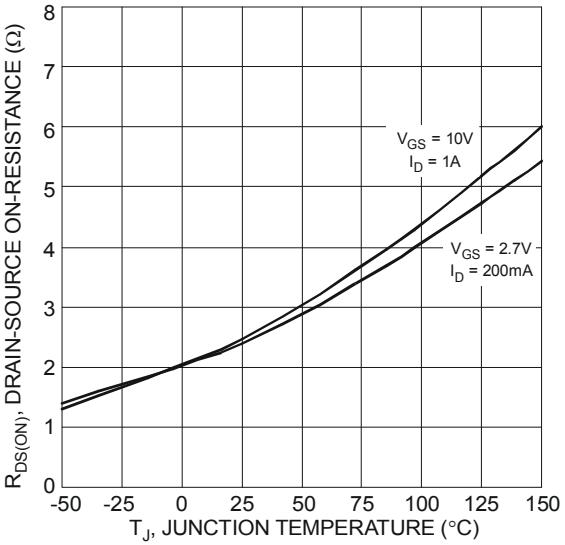

Figure 7 On-Resistance Variation with Temperature

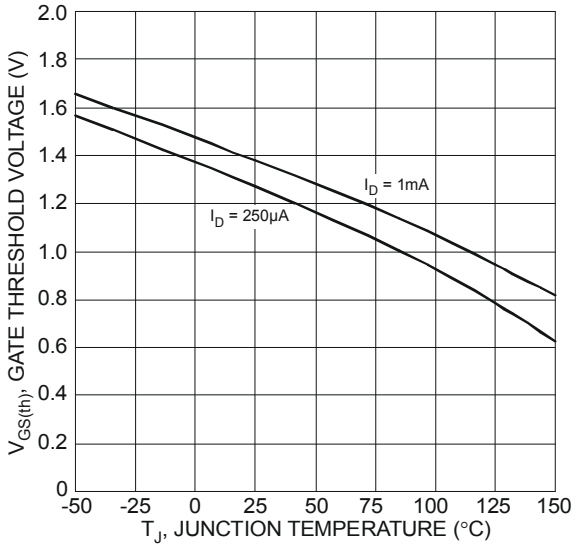

Figure 8 Gate Threshold Variation vs. Ambient Temperature

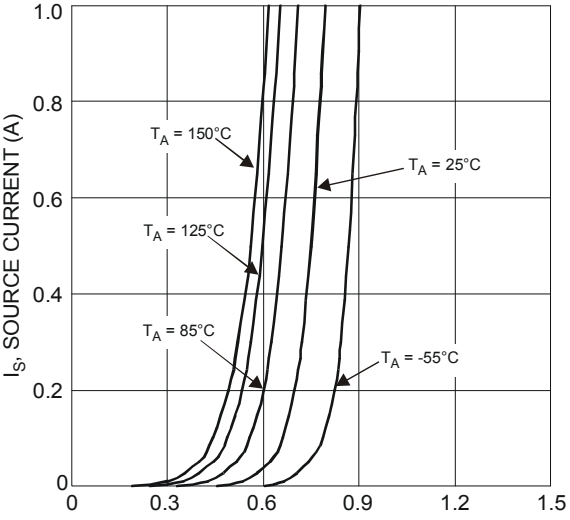

Figure 9 Diode Forward Voltage vs. Current

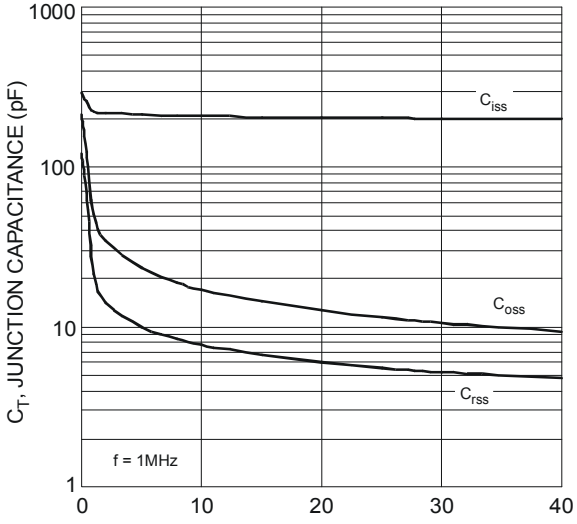

Figure 10 Typical Junction Capacitance

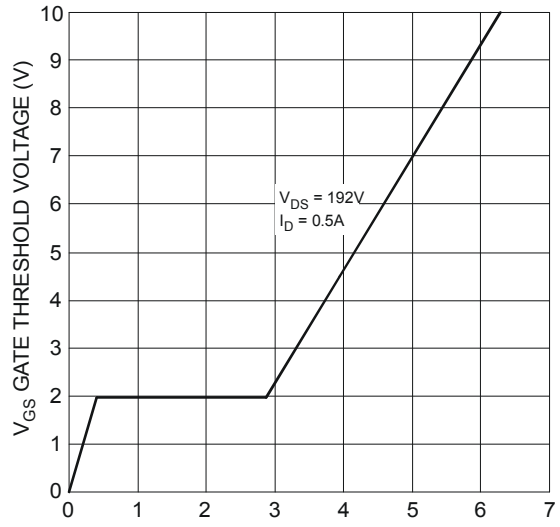

Figure 11 Gate Charge

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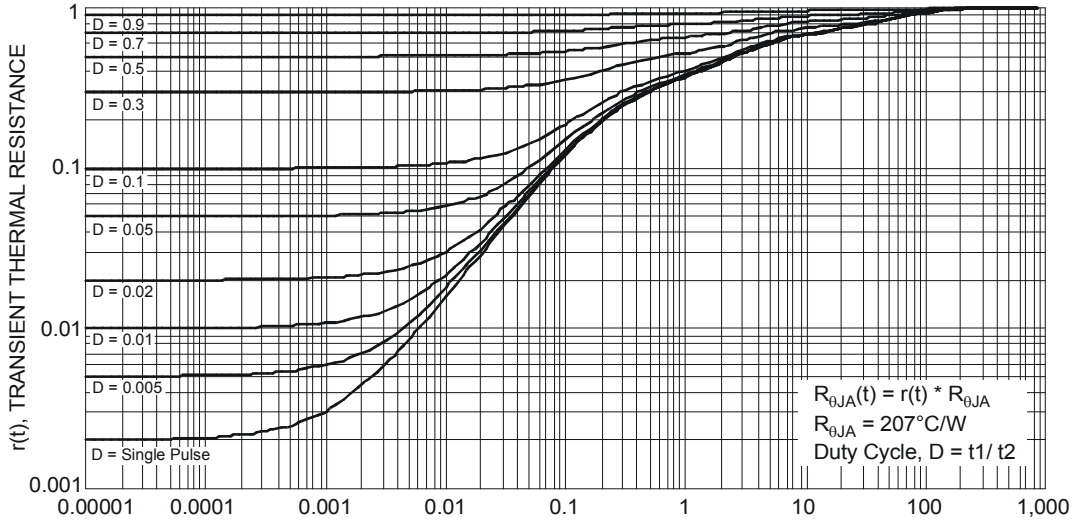
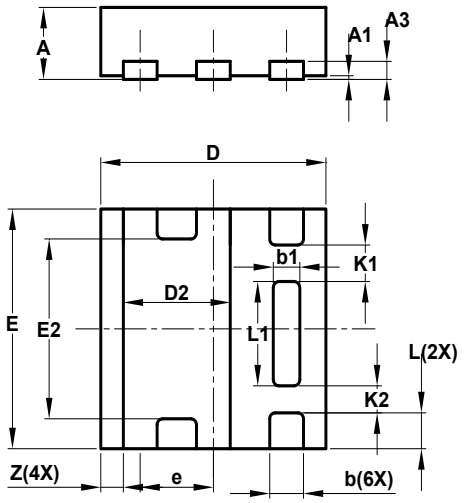


Figure 12 Transient Thermal Resistance

Package Outline Dimensions

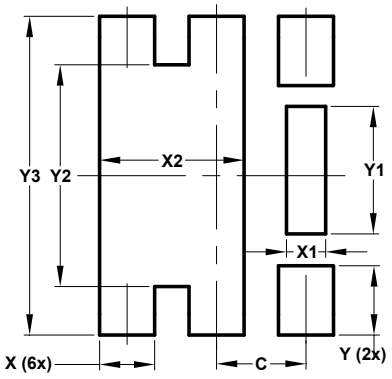
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



U-DFN2020-6 Type E			
Dim	**Min**	**Max**	**Typ**
A	0.57	0.63	0.60
A1	0	0.05	0.03
A3	—	—	0.15
b	0.25	0.35	0.30
b1	0.185	0.285	0.235
D	1.95	2.05	2.00
D2	0.85	1.05	0.95
E	1.95	2.05	2.00
E2	1.40	1.60	1.50
e	—	—	0.65
L	0.25	0.35	0.30
L1	0.82	0.92	0.87
K1	—	—	0.305
K2	—	—	0.225
Z	—	—	0.20
All Dimensions in mm			

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
C	0.650
X	0.400
X1	0.285
X2	1.050
Y	0.500
Y1	0.920
Y2	1.600
Y3	2.300

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